

-	1243	(((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and ((oxidiz\$ oxidat\$ oxide) with (gate transistor fet mosfet nfet nmosfet))	USPAT; US-PGPUB	2004/07/08 15:16
-	572	(((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and ((oxidiz\$ oxidat\$) with (gate transistor fet mosfet nfet nmosfet))	USPAT; US-PGPUB	2004/07/08 15:17
-	80	((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and (stress\$ tensile compressive)) not (@ad>20030923 or @rlad>20030923)) and ((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and ((oxidiz\$ oxidat\$) with (gate transistor fet mosfet nfet nmosfet)))	USPAT; US-PGPUB	2004/07/08 15:17
-	78	((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and (stress\$ tensile compressive)) not (@ad>20030923 or @rlad>20030923)) and ((((((438/199) or (438/218) or (438/229) or (438/230) or (438/231) or (438/232) or (438/233)).CCLS.) or ((438/279).CCLS.)) and (CMOS CMOSFET complementary)) and ((oxidiz\$ oxidat\$) with (gate transistor fet mosfet nfet nmosfet)))) not ((nmos pmos cmos nfet pfet cmosfet nmosfet pmosfet) and ((gate transistor fet mosfet) same ((polysilicon poly polysi) with (oxidation oxidized oxidizing oxidate oxidating oxidize)) same stress\$))	USPAT; US-PGPUB	2004/07/08 15:46
-	76828	cmos Cmosfet	USPAT; US-PGPUB	2004/07/08 15:47
-	2407	(cmos Cmosfet) and (mask with (nitride and (PR photoresist)))	USPAT; US-PGPUB	2004/07/08 15:56
-	182	(cmos Cmosfet) and (mask with (nitride near2 (PR photoresist)))	USPAT; US-PGPUB	2004/07/08 15:56
-	91	(cmos Cmosfet) and (mask near2 (nitride near2 (PR photoresist)))	USPAT; US-PGPUB	2004/07/08 15:56
-	0	(cmos Cmosfet) and (mask near2 (nitride near2 (PR photoresist)) with "or")	USPAT; US-PGPUB	2004/07/08 15:56
-	0	(cmos Cmosfet) and (mask with (nitride near2 (PR photoresist))with "or")	USPAT; US-PGPUB	2004/07/08 15:56
-	0	(cmos Cmosfet) and (mask with (nitride and (PR photoresist))with "or")	USPAT; US-PGPUB	2004/07/08 16:06
-	0	(cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted) with (nfet nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 16:07
-	0	(cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted) same (nfet nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 16:07
-	146	(cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted))	USPAT; US-PGPUB	2004/07/08 17:18
-	6	(cmos Cmosfet) and ((silicide or salicide) with (remove) with (NFET nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 17:18
-	5	(cmos Cmosfet) and ((silicide Cossi tisi wsi mosi) with (remove) with (NFET nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 17:10

-	0	((cmos Cmosfet) and ((silicide Cosi tisi wsi mosi) with (remove) with (NFET nmos nmosfet))) not ((cmos Cmosfet) and ((silicide or salicide) with (remove) with (NFET nmos nmosfet)))	USPAT; US-PGPUB	2004/07/08 17:10
-	226	((jennifer near2 kennedy).xa.	USPAT; US-PGPUB	2004/07/08 17:14
-	77	((jennifer near2 kennedy).xa.) and silicide	USPAT; US-PGPUB	2004/07/08 17:14
-	14	((jennifer near2 kennedy).xa.) and ((silicide salicide cosi wsi tisi) with remov\$)	USPAT; US-PGPUB	2004/07/08 17:15
-	595	(cmos Cmosfet) and ((silicide or salicide) with (remov\$ with unreacted))	USPAT; US-PGPUB	2004/07/08 17:18
-	449	((cmos Cmosfet) and ((silicide or salicide) with (remov\$ with unreacted))) not ((cmos Cmosfet) and ((silicide or salicide) with (remove with unreacted)))	USPAT; US-PGPUB	2004/07/08 17:18
-	21	(cmos Cmosfet) and ((silicide or salicide) with (remov\$) with (NFET nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 17:27
-	21	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with (remov\$) with (NFET nmos nmosfet))	USPAT; US-PGPUB	2004/07/08 17:28
-	0	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with (remov\$ etching etched etch) with (NFET nmos nmosfet) with top)	USPAT; US-PGPUB	2004/07/08 17:28
-	126	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with (remov\$ etching etched etch) with (NFET nmos nmosfet gate transistor fet) with top)	USPAT; US-PGPUB	2004/07/08 17:29
-	126	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with (remov\$ etching etched etch) with (NFET nmos nmosfet gate transistor fet mosfet) with top)	USPAT; US-PGPUB	2004/07/08 17:30
-	19	(cmos Cmosfet) and ((silicide or salicide cosi mosi tisi wsi) with ((remov\$ etching etched etch) near2 top) with (NFET nmos nmosfet gate transistor fet mosfet))	USPAT; US-PGPUB	2004/07/08 19:07
-	19	"5828131"	USPAT; US-PGPUB	2004/07/08 19:08
-	1	("5828131").PN.	USPAT; US-PGPUB	2004/07/08 19:07
-	1	"20020031909"	USPAT; US-PGPUB	2004/07/08 19:09
-	0	"200400087160"	USPAT; US-PGPUB	2004/07/08 19:09
-	1	"20040087160"	USPAT; US-PGPUB	2004/07/08 19:09